

Fig. 1a

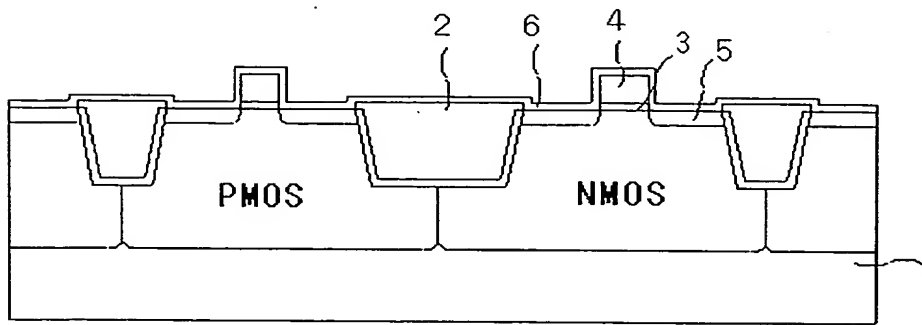


Fig. 1b

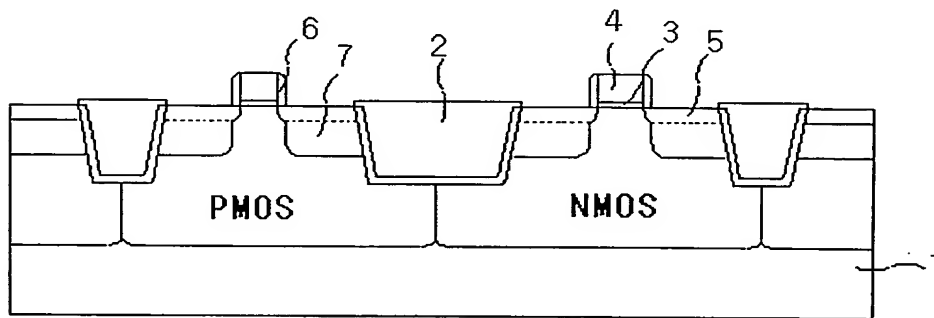


Fig. 1c

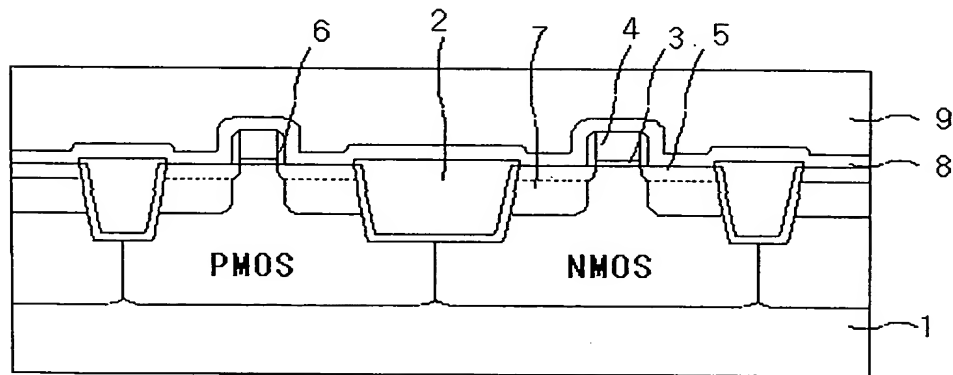


Fig. 1d

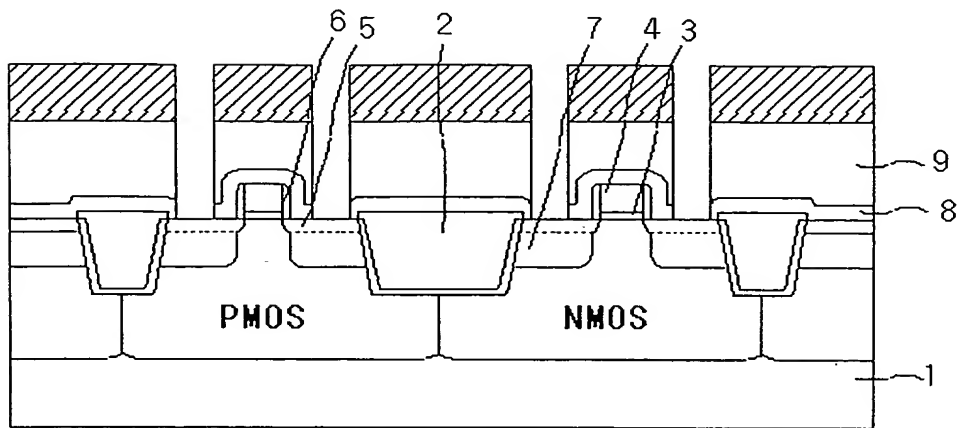


Fig. 2a

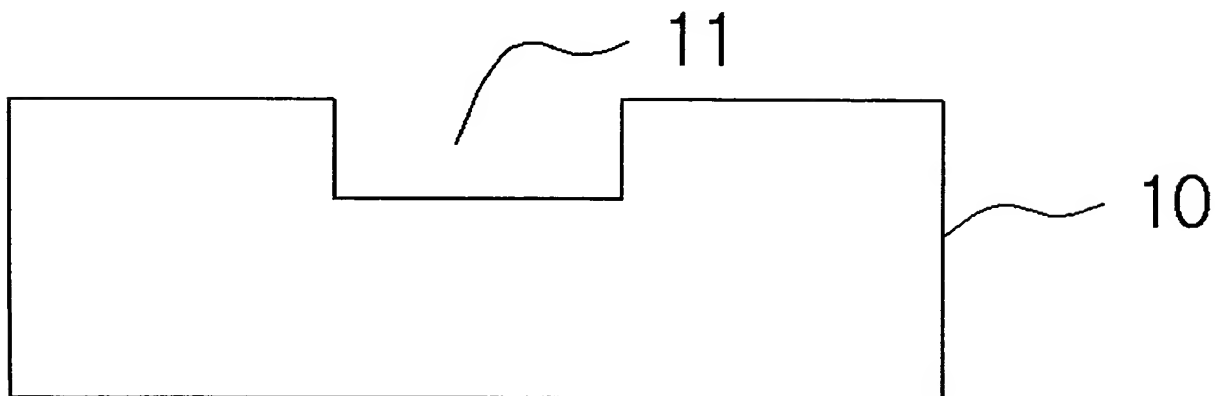


Fig. 2b

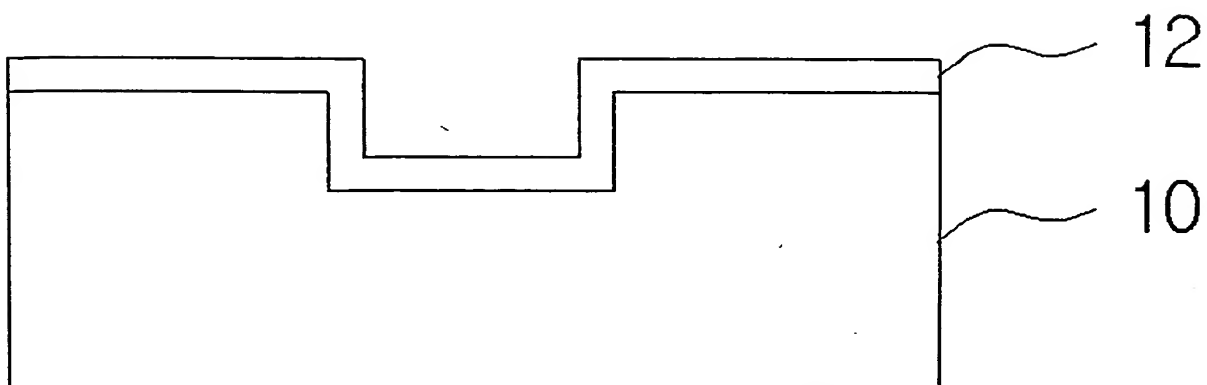


Fig. 2c

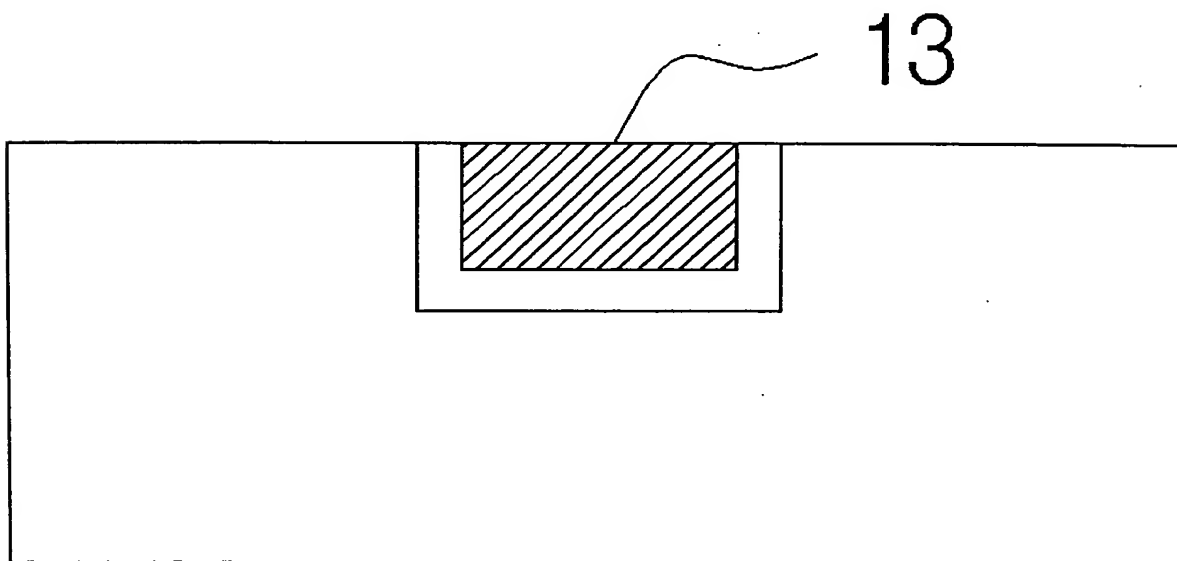


Fig. 2d

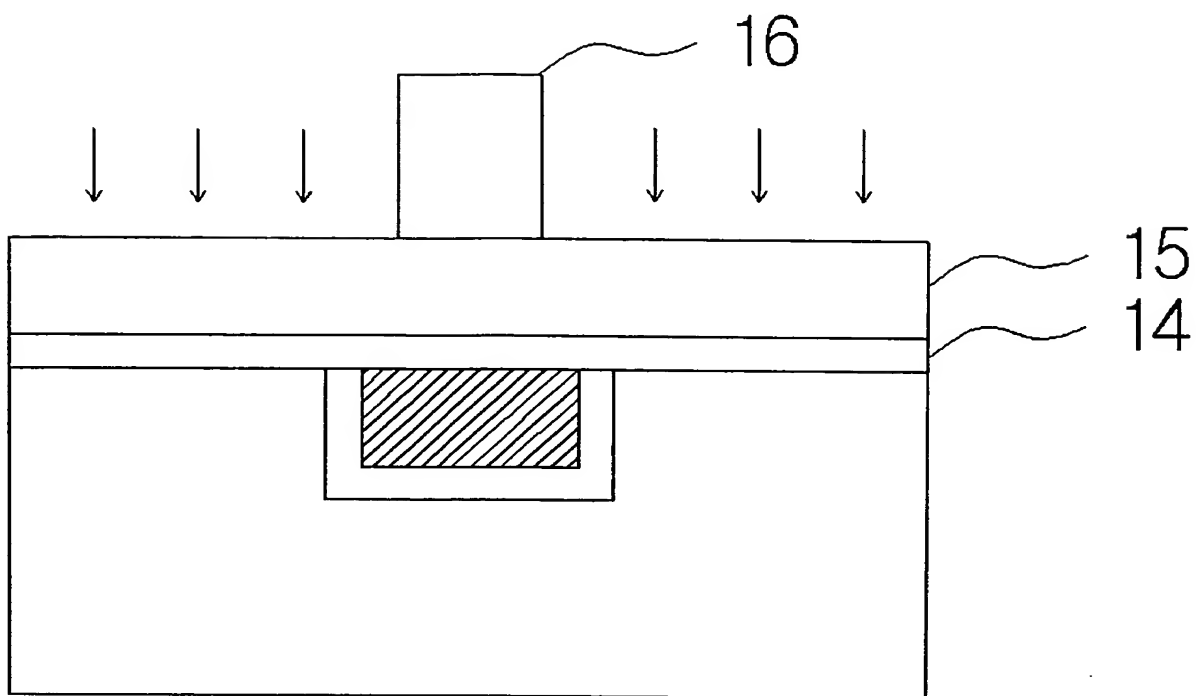


Fig. 2e

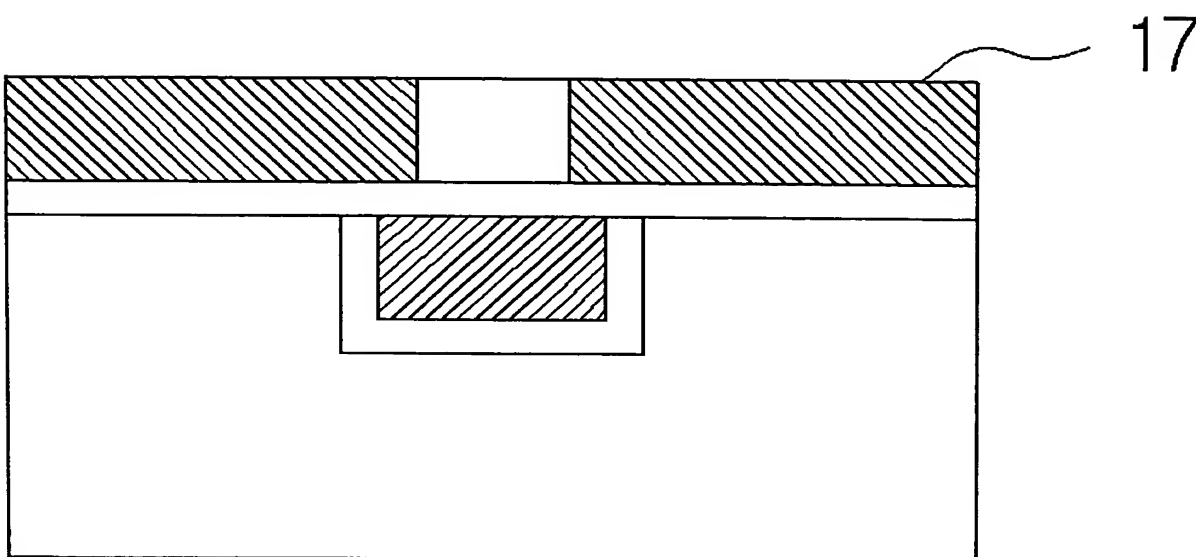


Fig. 1 is a cross-sectional view of a semiconductor device. It shows a substrate 18 with a top layer 19. The top layer 19 contains a central rectangular region with diagonal hatching, flanked by two smaller rectangular regions with diagonal hatching. Below the top layer 19 is a layer with diagonal hatching, and below that is a layer with a central rectangular region having diagonal hatching.